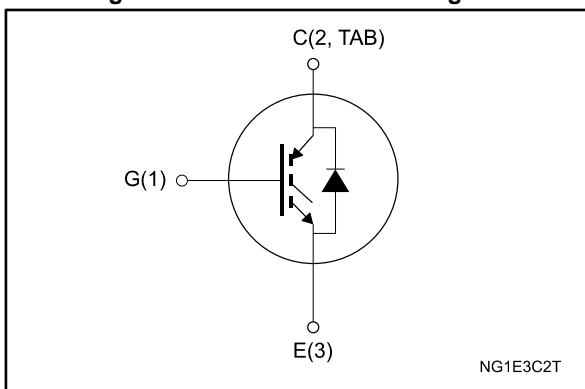


Trench gate field-stop IGBT, M series 650 V, 10 A low-loss in TO-247 package

Datasheet - production data



Figure 1: Internal schematic diagram



Features

- 6 μ s of short-circuit withstand time
- $V_{CE(sat)} = 1.55$ V (typ.) @ $I_c = 10$ A
- Tight parameter distribution
- Safer paralleling
- Positive $V_{CE(sat)}$ temperature coefficient
- Low thermal resistance
- Soft and very fast recovery antiparallel diode
- Maximum junction temperature: $T_J = 175$ °C

Applications

- Motor control
- UPS
- PFC
- General purpose inverter

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the M series IGBTs, which represent an optimal balance between inverter system performance and efficiency where low-loss and short-circuit functionality are essential. Furthermore, the positive $V_{CE(sat)}$ temperature coefficient and tight parameter distribution result in safer paralleling operation.

Table 1: Device summary

Order code	Marking	Package	Packing
STGW10M65DF2	G10M65DF2	TO-247	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
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3	Test circuits	12
4	Package information	13
	4.1 TO-247 package information	13
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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$ V)	650	V
I_C	Continuous collector current at $T_C = 25$ °C	20	A
	Continuous collector current at $T_C = 100$ °C	10	
$I_{CP}^{(1)}$	Pulsed collector current	40	A
V_{GE}	Gate-emitter voltage	± 20	V
I_F	Continuous forward current at $T_C = 25$ °C	20	A
	Continuous forward current at $T_C = 100$ °C	10	
$I_{FP}^{(1)}$	Pulsed forward current	40	A
P_{TOT}	Total dissipation at $T_C = 25$ °C	115	W
T_{STG}	Storage temperature range	- 55 to 150	°C
T_J	Operating junction temperature range	- 55 to 175	

Notes:

⁽¹⁾Pulse width limited by maximum junction temperature.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case IGBT	1.3	°C/W
R_{thJC}	Thermal resistance junction-case diode	2.08	
R_{thJA}	Thermal resistance junction-ambient	50	

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 4: Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 250\text{ }\mu\text{A}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 10\text{ A}$		1.55	2.0	V
		$V_{GE} = 15\text{ V}$, $I_C = 10\text{ A}$, $T_J = 125\text{ °C}$		1.9		
		$V_{GE} = 15\text{ V}$, $I_C = 10\text{ A}$, $T_J = 175\text{ °C}$		2.1		
V_F	Forward on-voltage	$I_F = 10\text{ A}$		1.5	2.25	V
		$I_F = 10\text{ A}$, $T_J = 125\text{ °C}$		1.3		
		$I_F = 10\text{ A}$, $T_J = 175\text{ °C}$		1.2		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	5	6	7	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 650\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 250	μA

Table 5: Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	840	-	pF
C_{oes}	Output capacitance		-	63	-	
C_{res}	Reverse transfer capacitance		-	16	-	
Q_g	Total gate charge	$V_{CC} = 520\text{ V}$, $I_C = 10\text{ A}$, $V_{GE} = 0\text{ to }15\text{ V}$ (see Figure 30: "Gate charge test circuit")	-	28	-	nC
Q_{ge}	Gate-emitter charge		-	6	-	
Q_{gc}	Gate-collector charge		-	12	-	

Table 6: IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 10\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 22\ \Omega$ (see Figure 29: "Test circuit for inductive load switching")		19	-	ns
t_r	Current rise time			7.4	-	ns
$(di/dt)_{on}$	Turn-on current slope			1086	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time			91	-	ns
t_f	Current fall time			92	-	ns
$E_{on}^{(1)}$	Turn-on switching energy			0.12	-	mJ
$E_{off}^{(2)}$	Turn-off switching energy			0.27	-	mJ
E_{ts}	Total switching energy			0.39	-	mJ
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 10\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 22\ \Omega$ $T_J = 175\text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching")		18	-	ns
t_r	Current rise time			9	-	ns
$(di/dt)_{on}$	Turn-on current slope			890	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time			90	-	ns
t_f	Current fall time			170	-	ns
$E_{on}^{(1)}$	Turn-on switching energy			0.26	-	mJ
$E_{off}^{(2)}$	Turn-off switching energy			0.4	-	mJ
E_{ts}	Total switching energy			0.66	-	mJ
t_{sc}	Short-circuit withstand time	$V_{CC} \leq 400\text{ V}$, $V_{GE} = 13\text{ V}$, $T_{Jstart} = 150\text{ }^\circ\text{C}$	10		-	μ s
		$V_{CC} \leq 400\text{ V}$, $V_{GE} = 15\text{ V}$, $T_{Jstart} = 150\text{ }^\circ\text{C}$	6		-	

Notes:

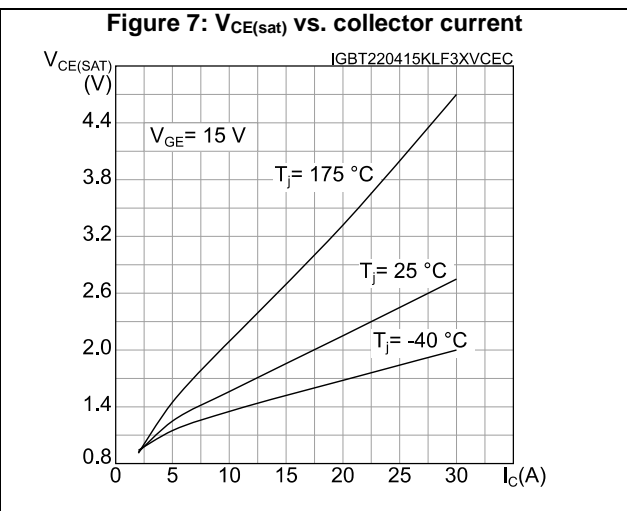
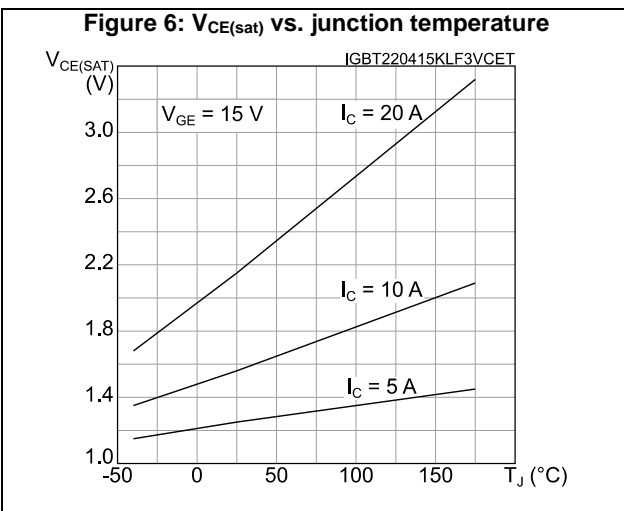
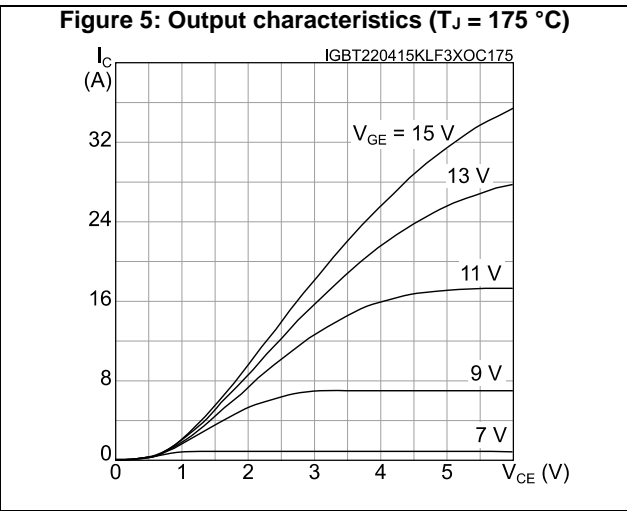
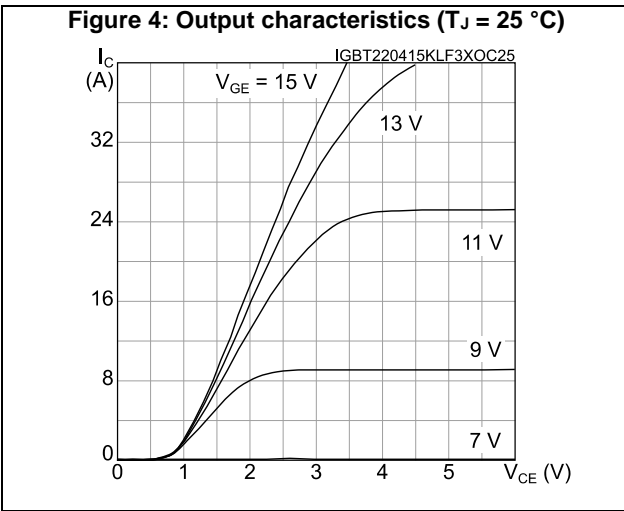
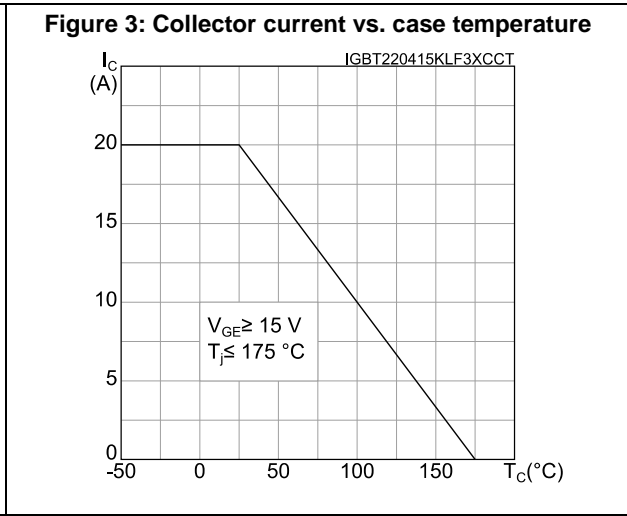
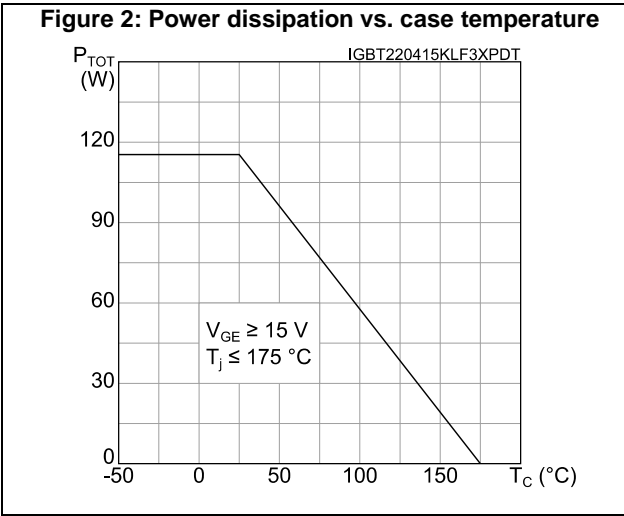
(1)Including the reverse recovery of the diode.

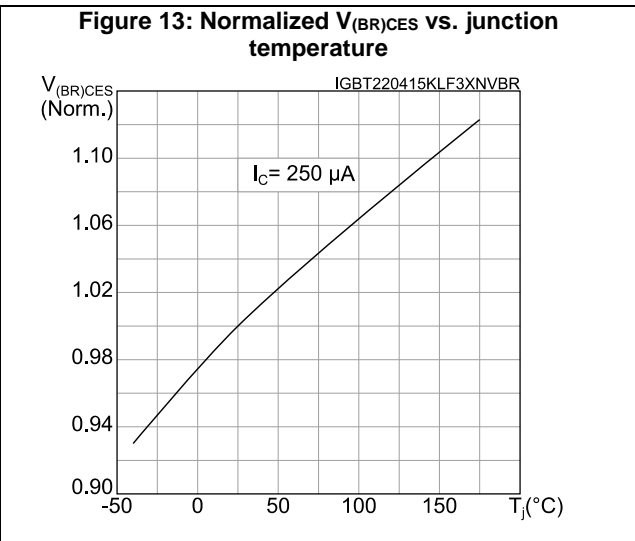
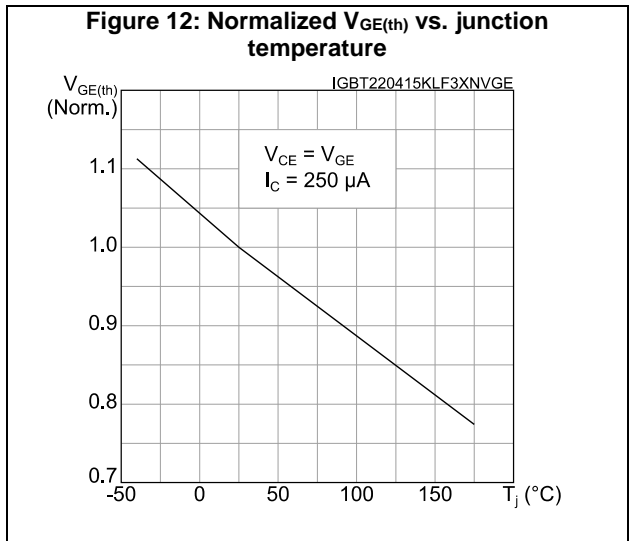
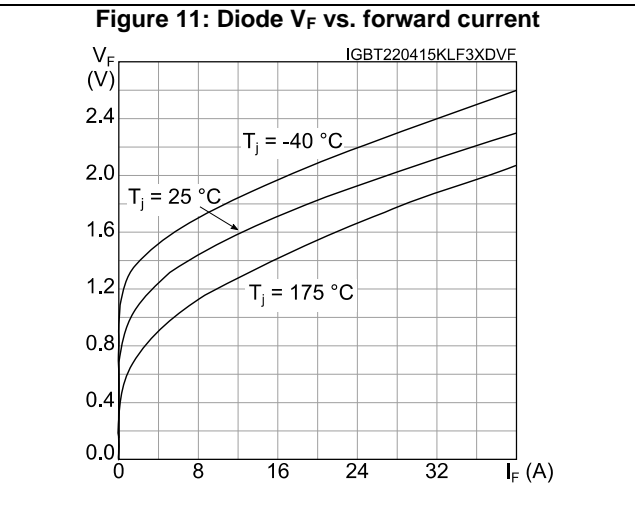
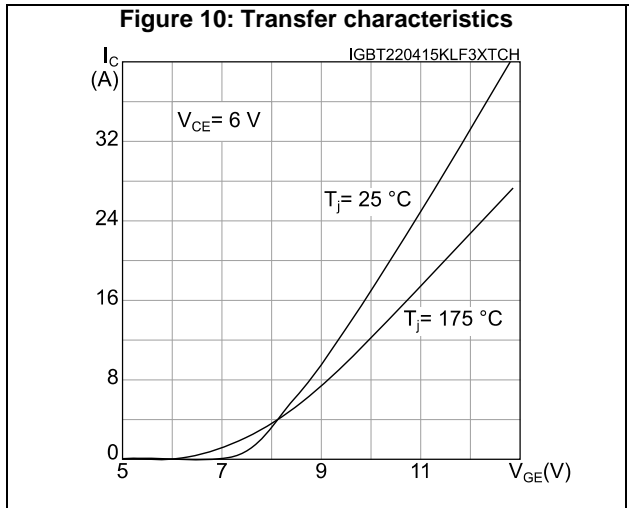
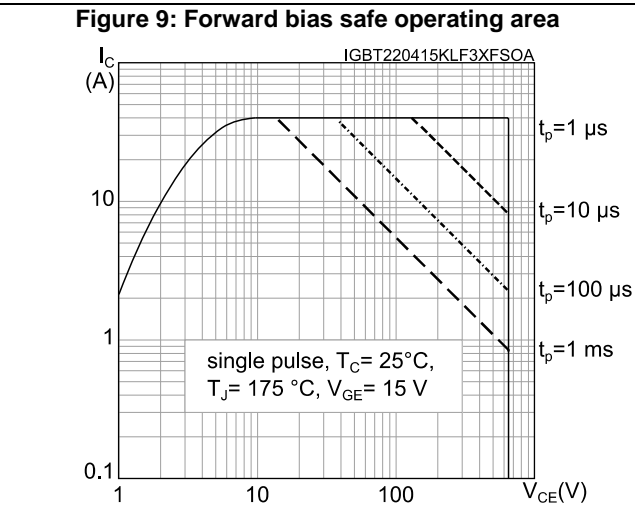
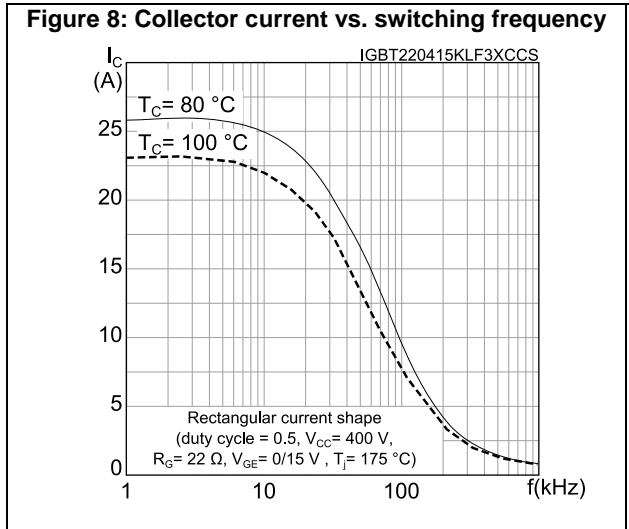
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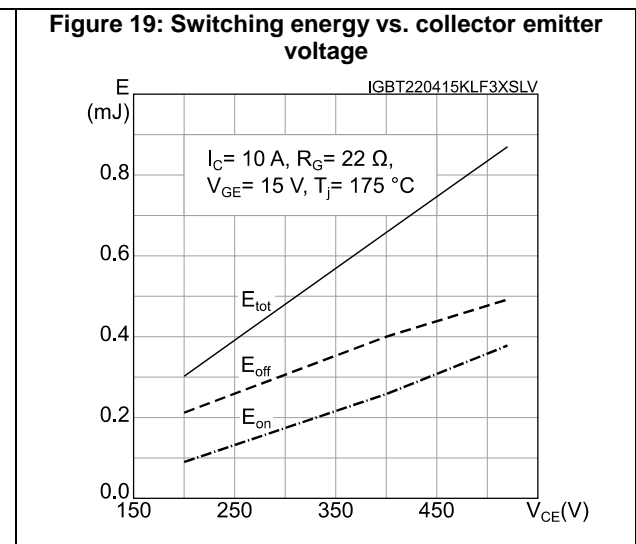
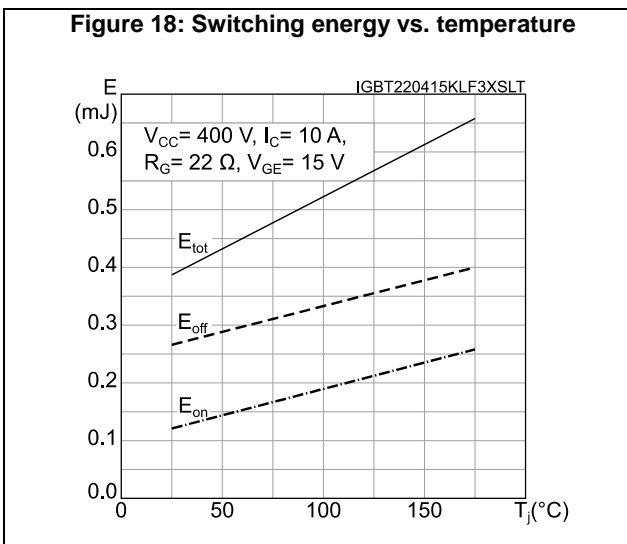
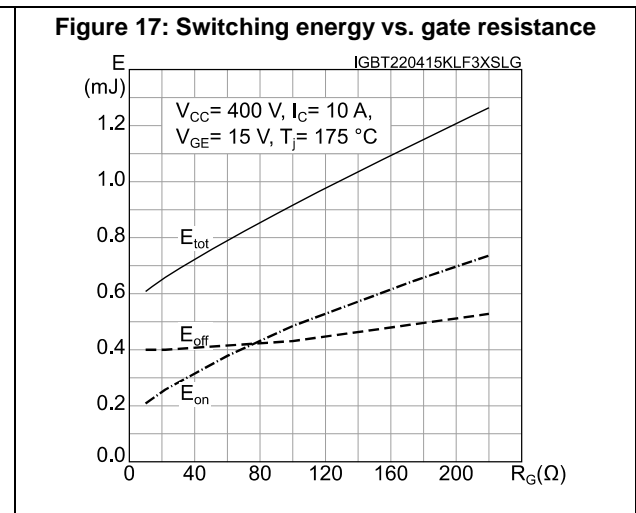
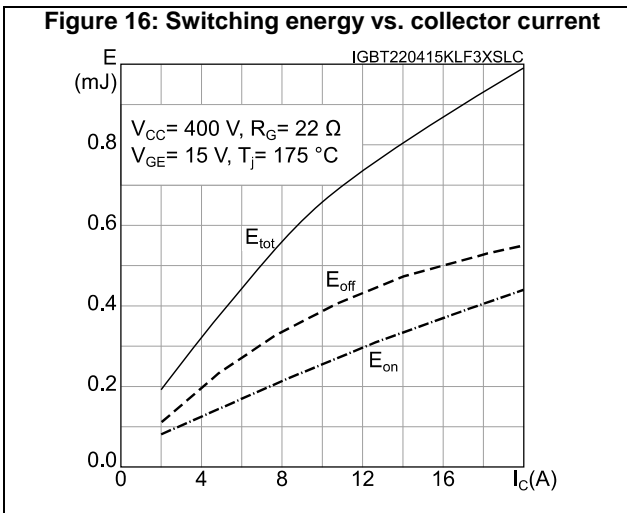
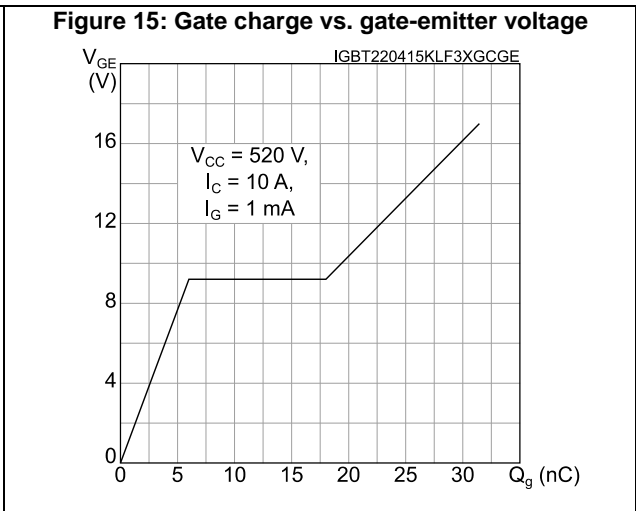
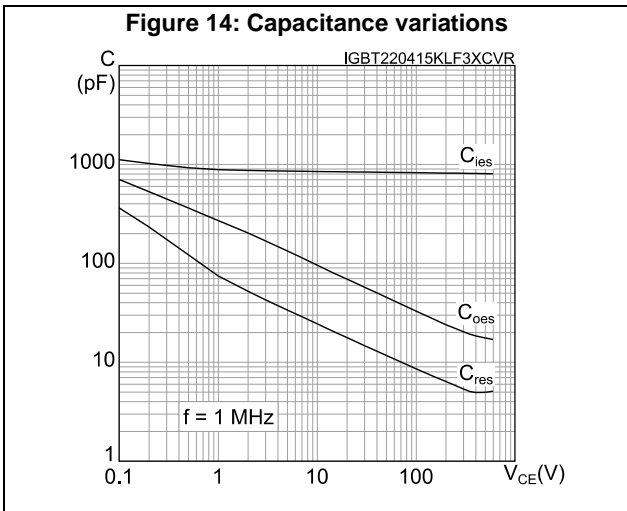
Table 7: Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 10\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $di/dt = 1000\text{ A}/\mu\text{s}$ (see Figure 29: "Test circuit for inductive load switching")	-	96	-	ns
Q_{rr}	Reverse recovery charge		-	373	-	nC
I_{rrm}	Reverse recovery current		-	13	-	A
dl_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	661	-	A/ μ s
E_{rr}	Reverse recovery energy		-	52	-	μ J
t_{rr}	Reverse recovery time	$I_F = 10\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $di/dt = 1000\text{ A}/\mu\text{s}$, $T_J = 175\text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching")	-	201	-	ns
Q_{rr}	Reverse recovery charge		-	1352	-	nC
I_{rrm}	Reverse recovery current		-	19	-	A
dl_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	405	-	A/ μ s
E_{rr}	Reverse recovery energy		-	150	-	μ J

2.1 Electrical characteristics (curves)







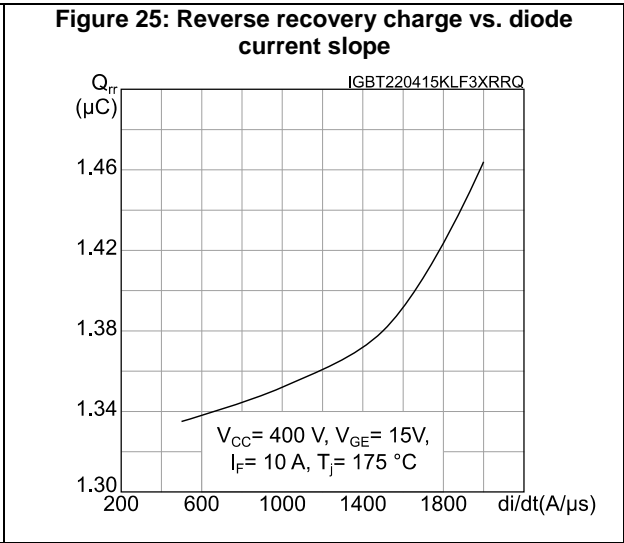
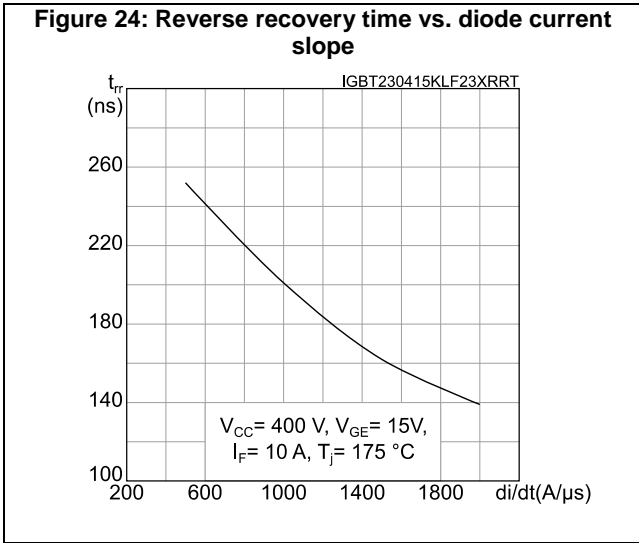
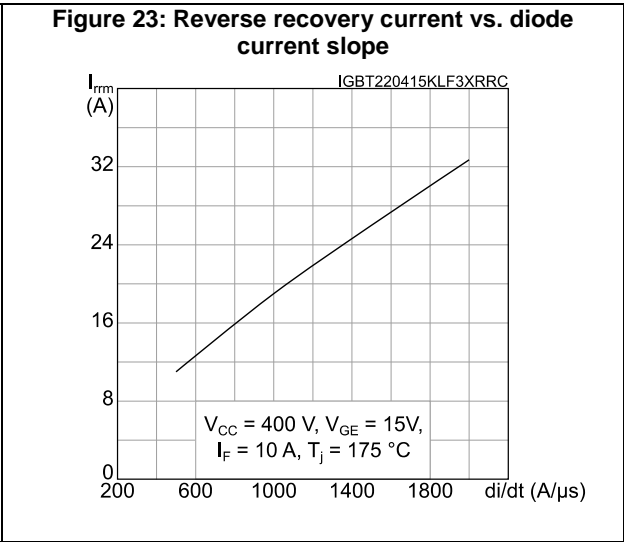
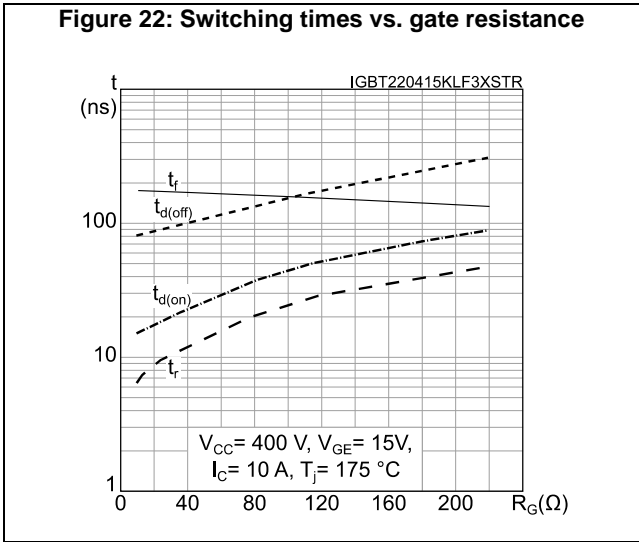
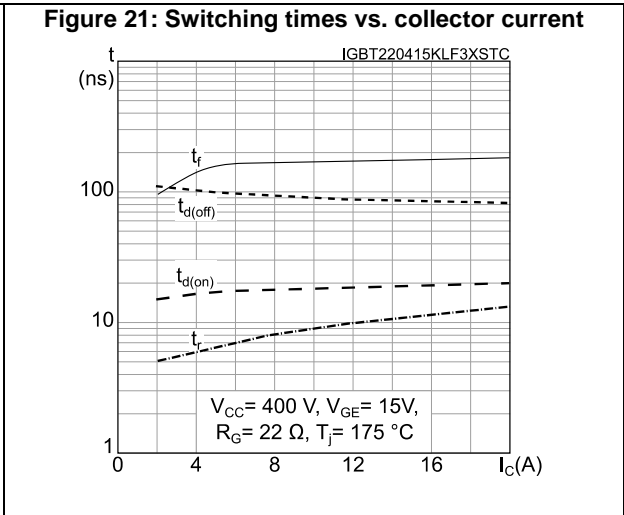
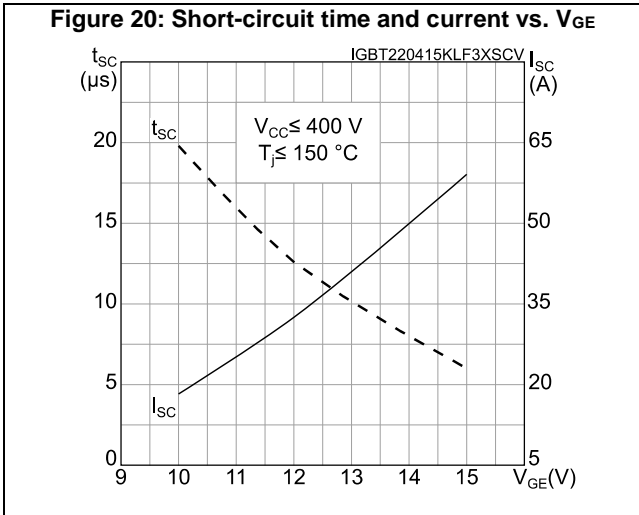


Figure 26: Reverse recovery energy vs. diode current slope

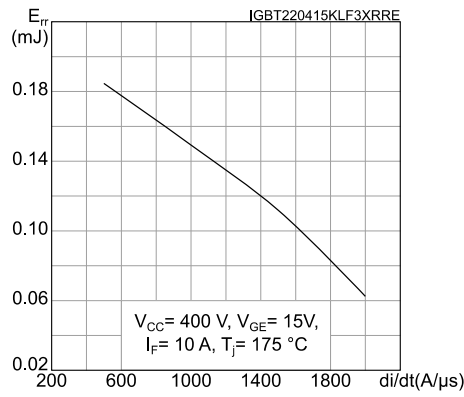


Figure 27: Thermal impedance for IGBT

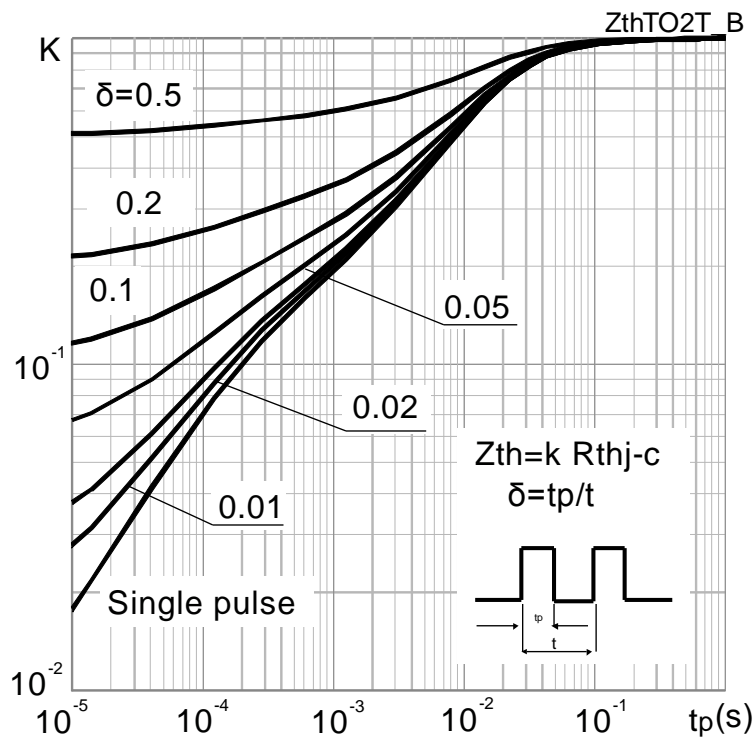
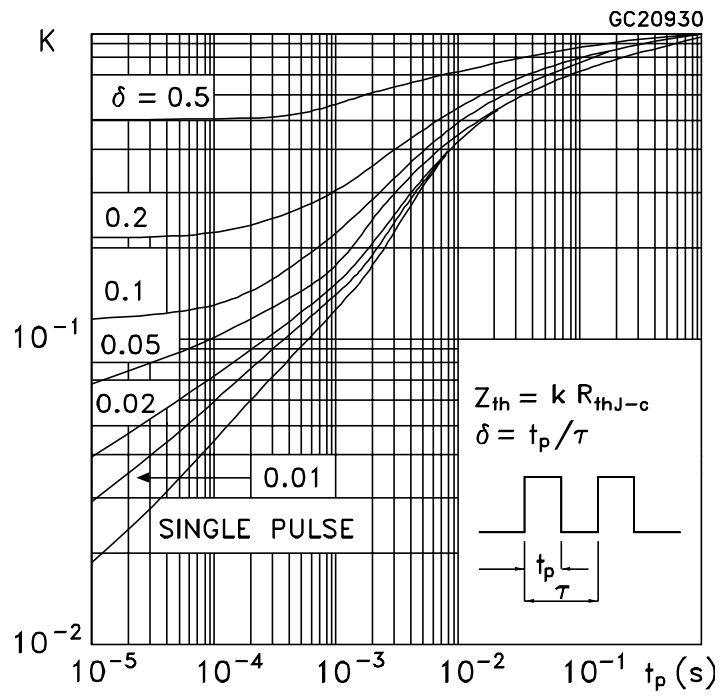
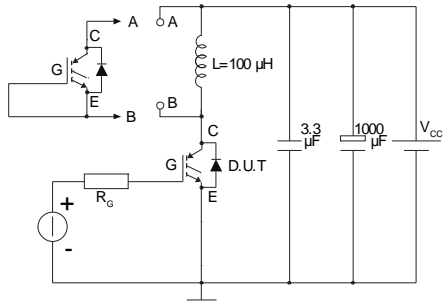


Figure 28: Thermal impedance for diode



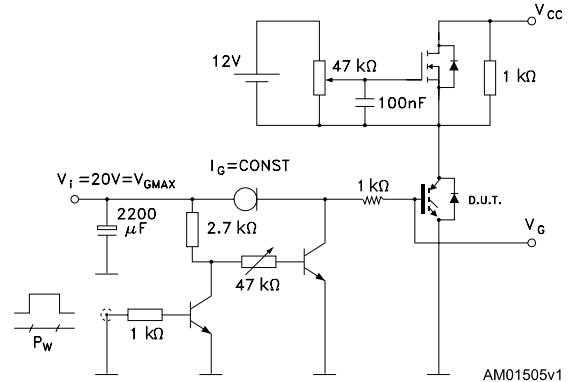
3 Test circuits

Figure 29: Test circuit for inductive load switching



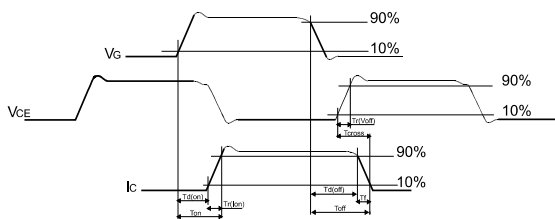
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Figure 30: Gate charge test circuit



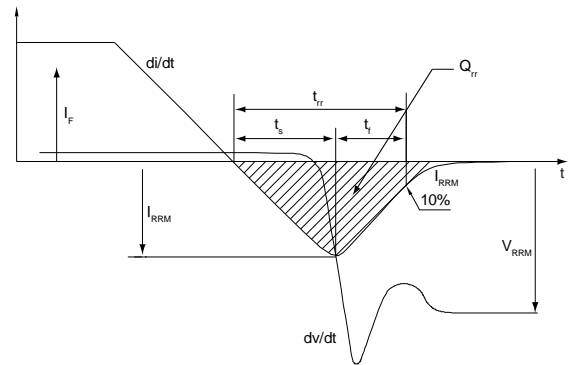
AM01505v1

Figure 31: Switching waveform



AM01506v1

Figure 32: Diode reverse recovery waveform



AM01507v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-247 package information

Figure 33: TO-247 package outline

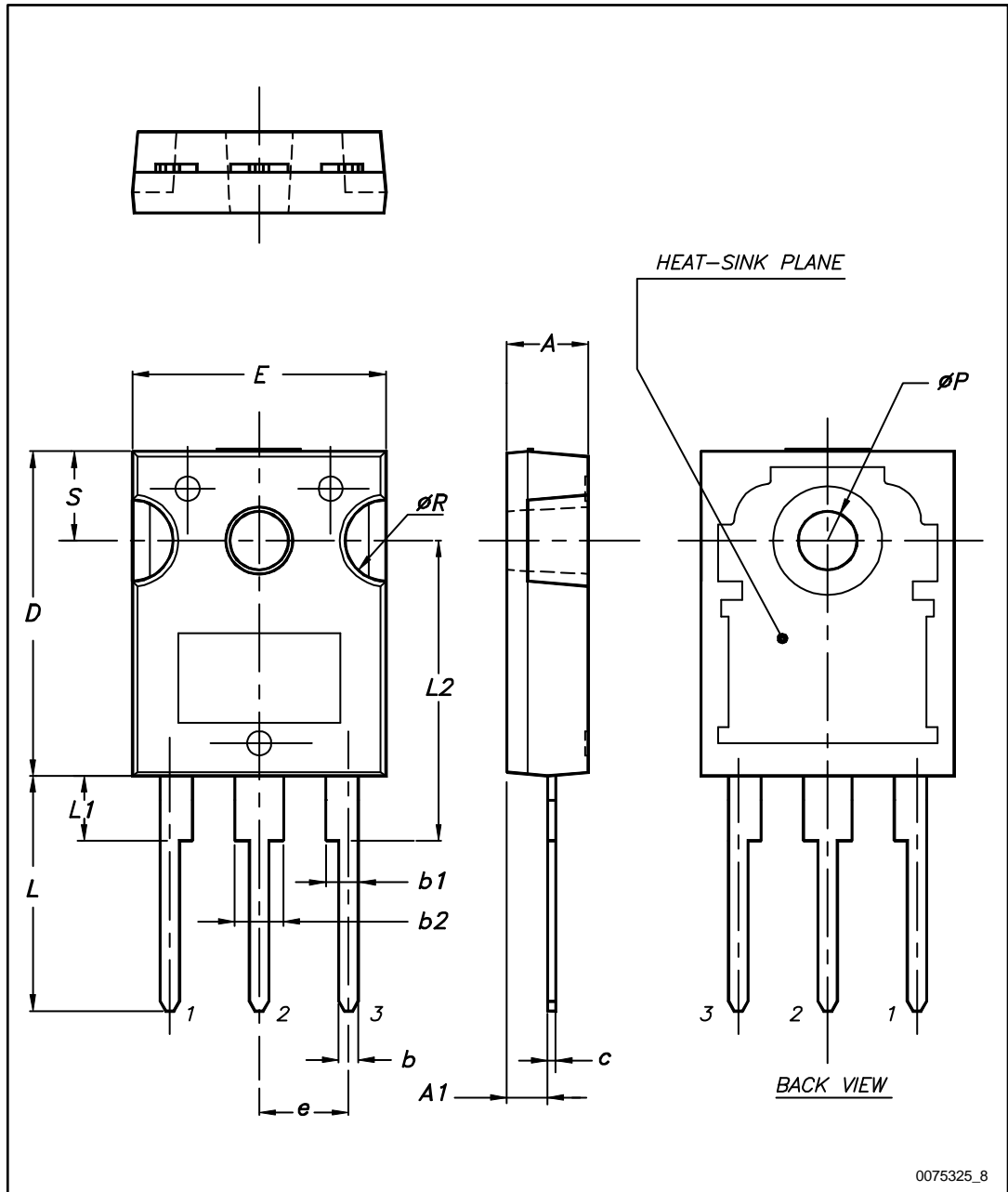


Table 8: TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

5 Revision history

Table 9: Document revision history

Date	Revision	Changes
08-Mar-2016	1	First release.
07-Apr-2017	2	Modified title, features and applications on cover page Modified <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 4: "Static characteristics"</i> and <i>Table 7: "Diode switching characteristics (inductive load)"</i> Minor text changes.